

Features

- Advanced 2nd generation SiC MOSFET technology
- High blocking voltage with low on-resistance
- High-speed switching with low capacitances
- Low switching loss
- RoHS compliant with Halogen-free

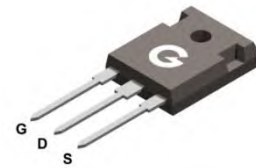
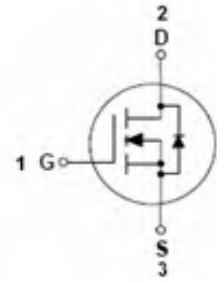
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Applications

- Solar PV inverters
- EV charging infrastructure
- Uninterruptible Power Supply
- Switch Mode Power Supplies
- Energy storage and battery formation
- Class D amplifiers

Mechanical Data

- Case: TO-247
- Molding Compound: UL Flammability Classification Rating 94V-0
- Terminals: Matte tin-plated leads; solderability-per MIL-STD-202, Method 208



TO-247

Ordering Information

Part Number	Package	Shipping Quantity	Marking Code
GSC2D65R025U	TO-247	30 pcs / Tube	2D65R025

Maximum Ratings (@ T_C = 25°C unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-to-Source Voltage	V _{DSS}	650	V
Gate-to-Source Voltage (transient)	V _{GSS}	-8/+22	V
Gate-to-Source Voltage (static)		-4/+18	
Continuous Drain Current (T _C = 25°C)	I _D	111	A
Continuous Drain Current (T _C = 100°C)		79	
Pulsed Drain Current	I _{DM}	230	A
Power Dissipation (T _C = 25°C)	P _D	357	W
Operating Junction Temperature Range	T _J	-40 ~ +175	°C
Storage Temperature Range	T _{STG}	-40 ~ +175	°C

Thermal Characteristics

Parameter	Symbol	Min.	Typ.	Max.	Unit
Thermal Resistance Junction-to-Case	R _{θJC}	-	0.42	-	°C/W

Electrical Characteristics (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Unit
Static Characteristics						
V _{DSS}	Drain-Source Breakdown Voltage	V _{GS} = 0V, I _D = 100μA	650	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = 650V, V _{GS} = 0V	-	-	10	μA
I _{GSS}	Gate-Body Leakage Current	V _{GS} = 18V, V _{DS} = 0V	-	-	250	nA
		V _{GS} = -4V, V _{DS} = 0V	-	-	-250	nA
On Characteristics						
R _{DS(ON)}	Drain-Source On-resistance *1	V _{GS} = 18V, I _D = 33.5A, T _J = 25°C	-	23	30	mΩ
		V _{GS} = 18V, I _D = 33.5A, T _J = 175°C	-	25	-	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = 10mA	2	2.7	4	V
R _G	Gate Resistance	V _{GS} = 0V, f = 1MHz	-	1.6	-	Ω
Dynamic Characteristics						
C _{ISS}	Input Capacitance	V _{GS} = 0V V _{DS} = 600V f = 100kHz	-	2162	-	pF
C _{OSS}	Output Capacitance		-	195	-	
C _{RSS}	Reverse Transfer Capacitance		-	14	-	
Switching Characteristics						
t _{d(ON)}	Turn-on Delay Time *2	V _{DD} = 400V V _{GS} = -4/18V I _D = 33.5A R _G = 2.5Ω L = 103μH	-	12	-	ns
t _r	Turn-on Rise Time *2		-	14	-	
t _{d(OFF)}	Turn-Off Delay Time *2		-	25	-	
t _f	Turn-Off Fall Time *2		-	8	-	
E _{on}	Turn-On Energy *2		-	63	-	μJ
E _{off}	Turn-Off Energy *2		-	31	-	
Q _G	Total Gate-Charge	V _{DD} = 400V	-	100	-	nC
Q _{GS}	Gate to Source Charge	V _{GS} = -4/18V	-	25	-	
Q _{GD}	Gate to Drain (Miller) Charge	I _D = 33.5A	-	28	-	
Source-Drain Diode Characteristics						
V _{SD}	Diode Forward Voltage *1	I _{SD} = 33.5A, V _{GS} = -4V, T _J = 25°C	-	4.2	-	V
		I _{SD} = 33.5A, V _{GS} = -4V, T _J = 175°C	-	3.9	-	
t _{rr}	Reverse Recovery Time	I _F = 33.5A, V _R = 400V	-	19	-	ns
Q _{rr}	Reverse Recovery Charge	dI/dt = 1862A/μs	-	230	-	nC

Notes:

- The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
- Guaranteed by design, not subject to production

Ratings and Characteristics Curves (@ $T_A = 25^\circ\text{C}$ unless otherwise specified)

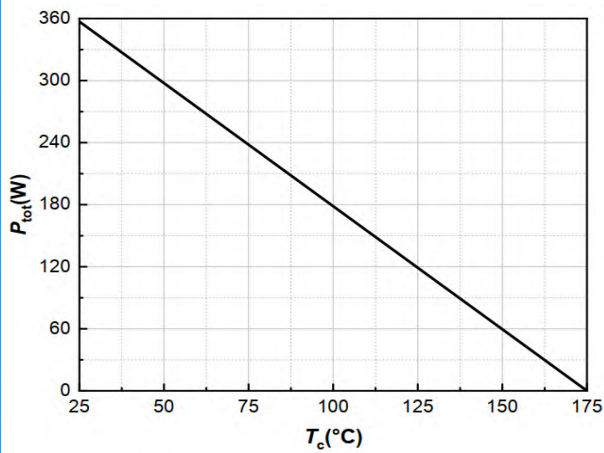


Fig 1 Power Dissipation

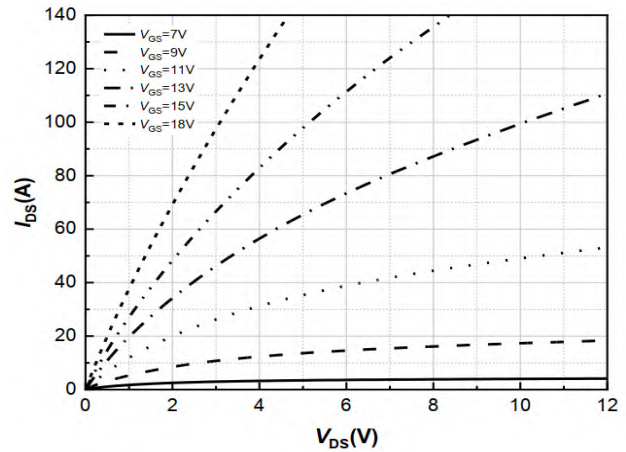


Fig 2 Typical Output Characteristics ($T_j = -40^\circ\text{C}$)

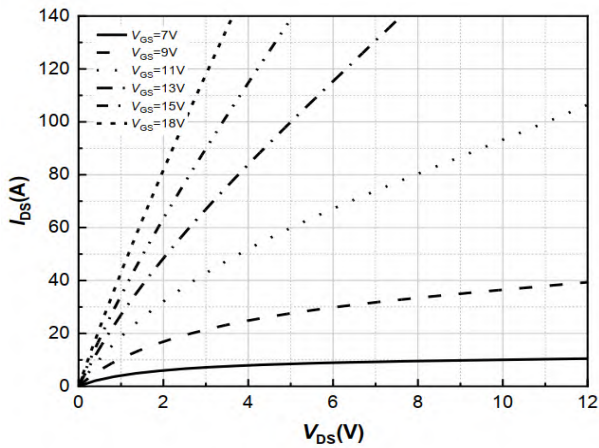


Fig 3 Typical Output Characteristics ($T_j = 25^\circ\text{C}$)

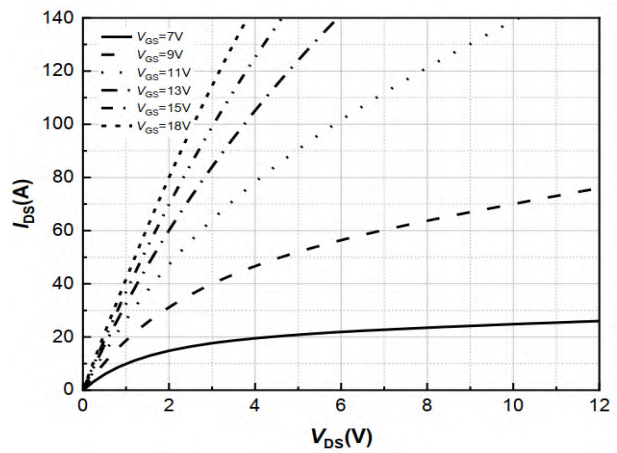


Fig 4 Typical Output Characteristics ($T_j = 175^\circ\text{C}$)

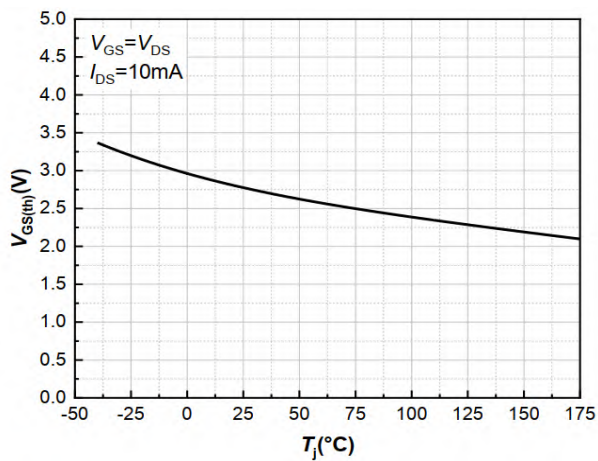


Fig 5 $V_{GS(th)}$ vs. Junction Temperature

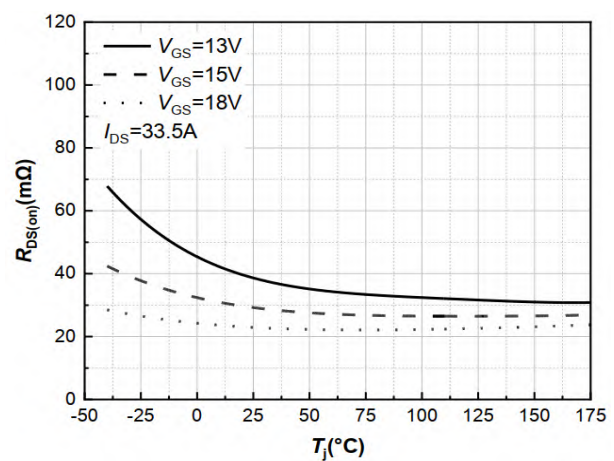


Fig 6 On-Resistance vs. Junction Temperature

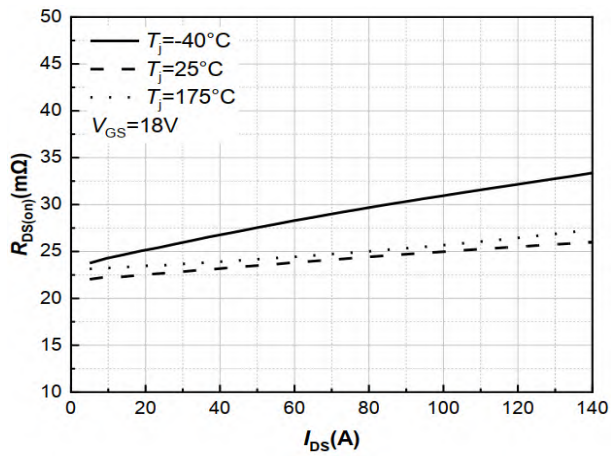


Fig 7 On-Resistance vs. Drain Current

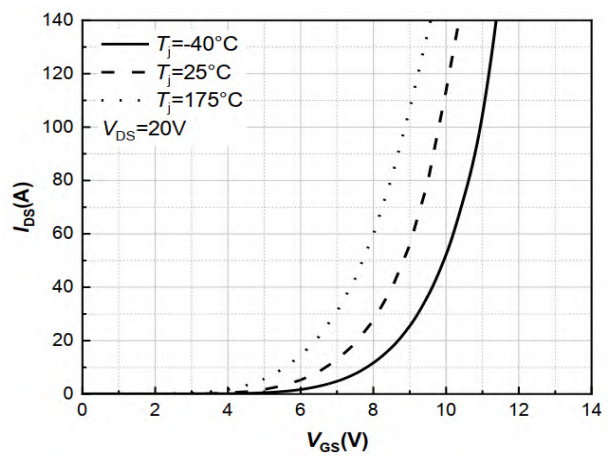


Fig 8 Transfer Characteristics

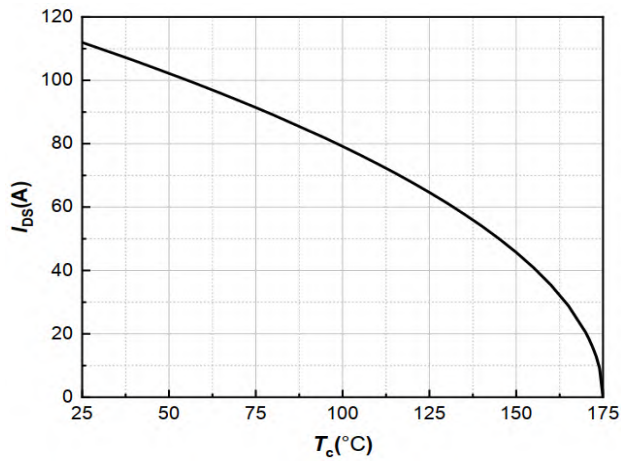


Fig 9 Drain Current

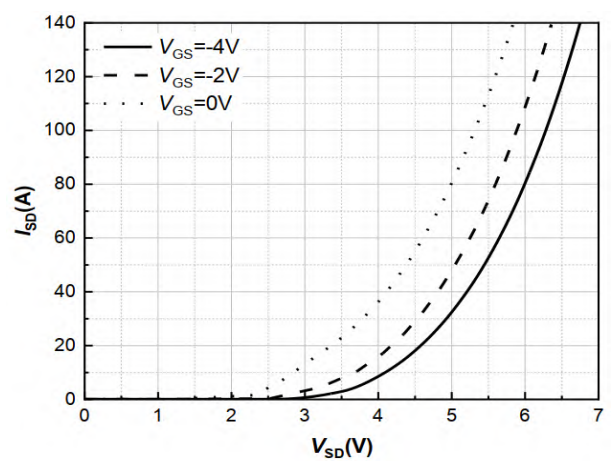


Fig 10 Body-Diode Characteristics ($T_J = -40^\circ\text{C}$)

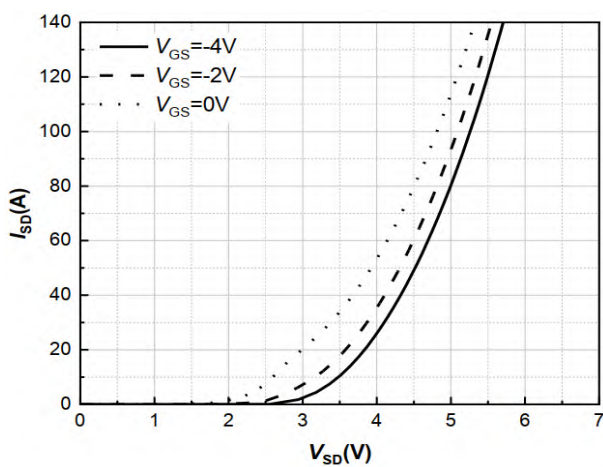


Fig 11 Body-Diode Characteristics ($T_J = 25^\circ\text{C}$)

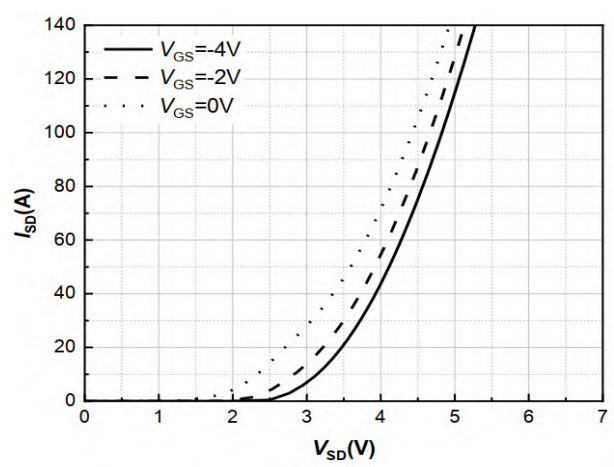


Fig 12 Body-Diode Characteristics ($T_J = 175^\circ\text{C}$)

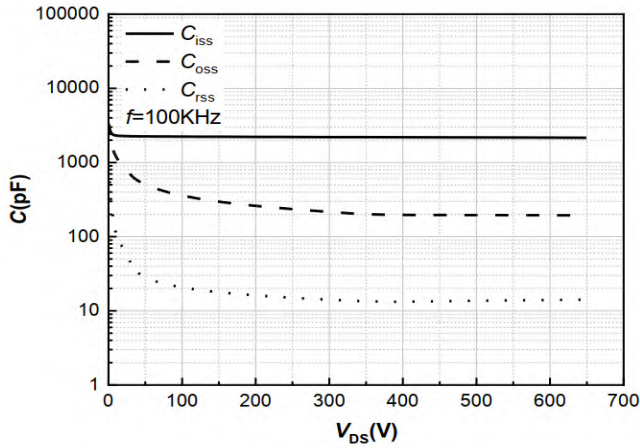


Fig 13 Capacitance Characteristics

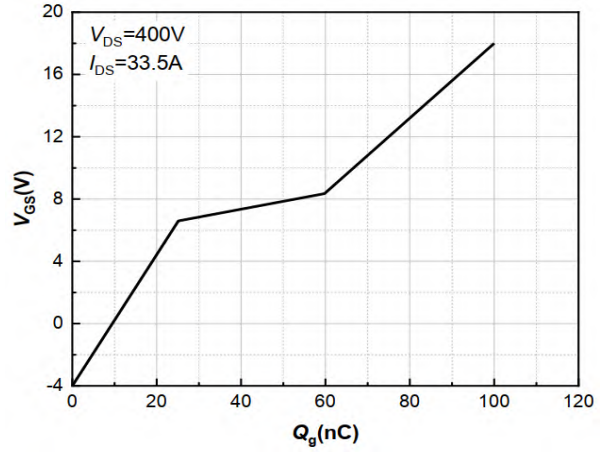


Fig 14 Gate-Charge Characteristics

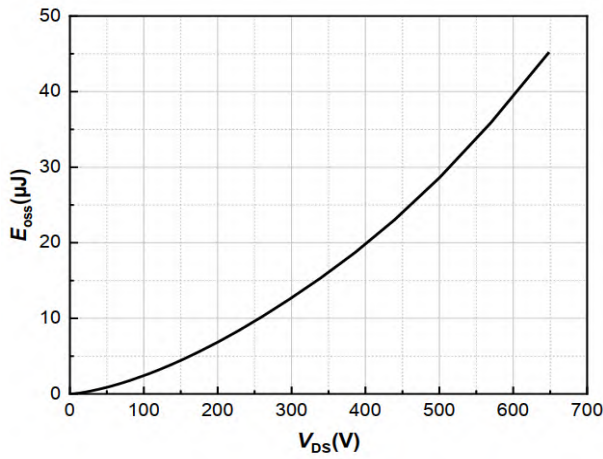


Fig 15 Output Capacitor Stored Energy

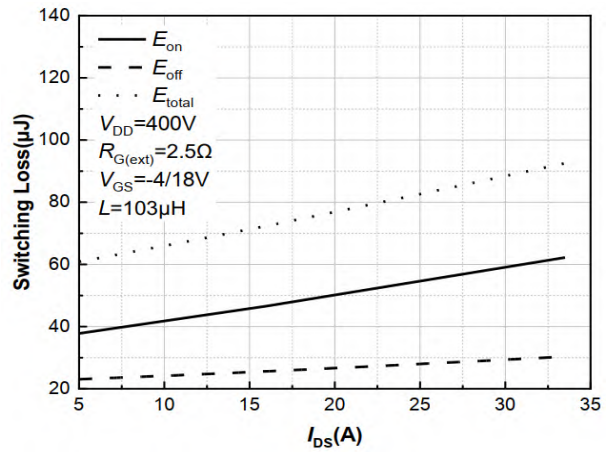


Fig 16 Clamped Inductive Switching Energy vs.
Drain Current

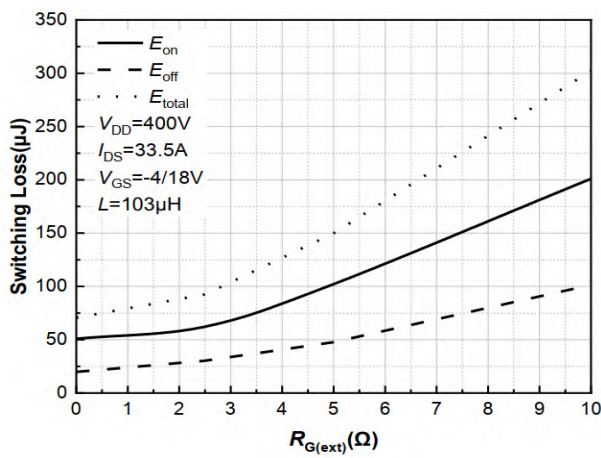


Fig 17 Clamped Inductive Switching Energy vs. R_G

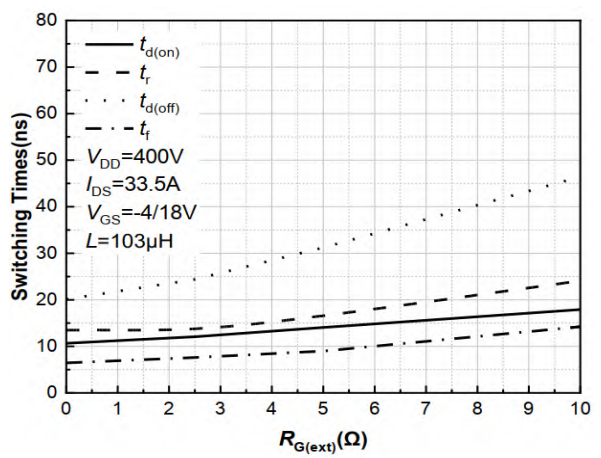


Fig 18 Switching Times vs. R_G

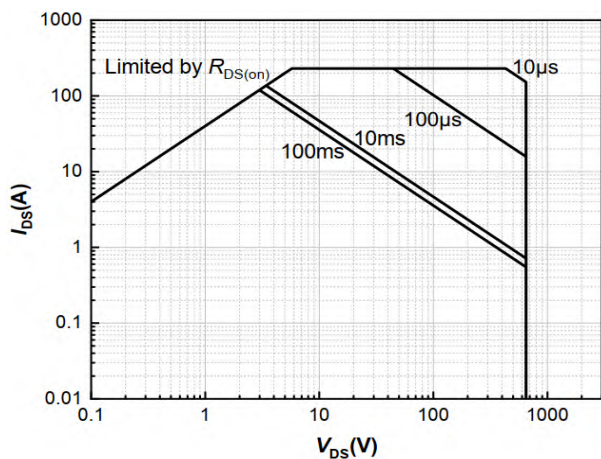


Fig 19 Safe Operating Area

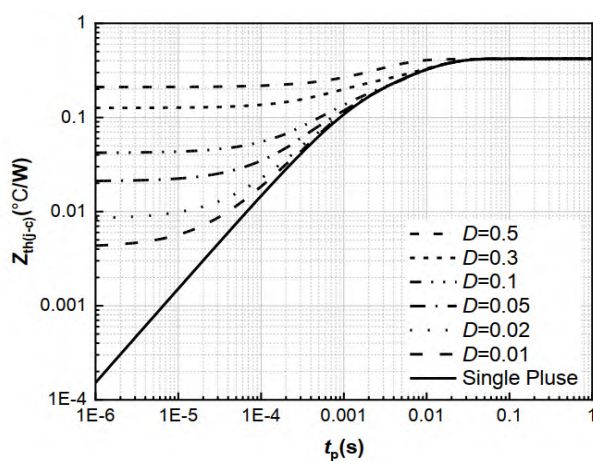
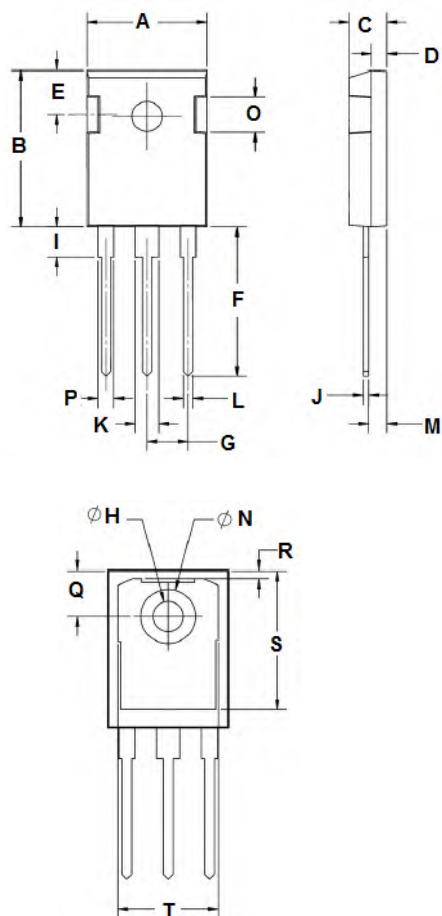


Fig 20 Maximum transient thermal impedance

Package Outline Dimensions (Unit: mm)



TO-247		
Dimension	Min.	Max.
A	15.50	16.10
B	20.70	21.30
C	4.70	5.30
D	1.80	2.20
E	5.20	5.80
F	19.70	20.30
G	5.20	5.60
H	3.30	3.70
I	3.90	4.30
J	0.50	0.70
K	2.80	3.20
L	1.00	1.40
M	2.20	2.60
N	7.00	7.20
O	4.90	5.30
P	1.80	2.20
Q	5.70	5.90
R	0.80	1.20
S	17.00	17.80
T	13.60	14.20